

0.9V Drive Nch MOSFET

RYU002N05

Structure

Silicon N-channel MOSFET

Features

- 1) High speed switing.
- 2) Small package(UMT3).
- 3)Ultra low voltage drive(0.9V drive).

Application

Switching

Packaging specifications

	Package	Taping	
Type	Code	T306	
	Basic ordering unit (pieces)	3000	
RYU002N0	0		

• Absolute maximum ratings $(T_a = 25^{\circ}C)$

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	50	V
Gate-source voltage		V_{GSS}	±8	V
Drain current	Continuous	I _D	±200	mA
	Pulsed	I _{DP} *1	±800	mA
Source current	Continuous	I _S	150	mA
(Body Diode)	Pulsed	I _{SP} *1	800	mA
Power dissipation		P _D *2	200	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

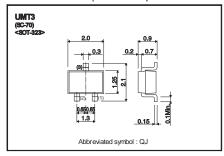
^{*1} Pw≤10µs, Duty cycle≤1%

● Thermal resistance

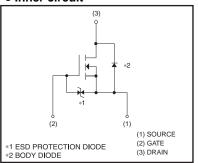
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	625	°C/W

^{*} Each terminal mounted on a recommended land.

● Dimensions (Unit : mm)



• Inner circuit



^{*2} Each terminal mounted on a recommended land.

ullet Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	±10	μA	$V_{GS}=\pm 8V, V_{DS}=0V$
Drain-source breakdown voltage	V _{(BR)DSS}	50	-	-	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	1	-	1	μA	V_{DS} =50V, V_{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.3	-	0.8	٧	V_{DS} =10V, I_{D} =1mA
		1	1.6	2.2	Ω	$I_D = 200 \text{mA}, V_{GS} = 4.5 \text{V}$
Otatia duain accusa an atata	R _{DS (on)}	1	1.7	2.4		I _D =200mA, V _{GS} =2.5V
Static drain-source on-state resistance		-	2.0	2.8		I _D =200mA, V _{GS} =1.5V
rosistanos		-	2.2	3.3		I _D =100mA, V _{GS} =1.2V
		1	3.0	9.0		I _D =10mA, V _{GS} =0.9V
Forward transfer admittance	I Y _{fs} I*	0.2	-	-	S	I _D =200mA, V _{DS} =10V
Input capacitance	C _{iss}	1	26	-	pF	V _{DS} =10V
Output capacitance	C _{oss}	-	6	-	pF	V _{GS} =0V
Reverse transfer capacitance	C_{rss}	-	3	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	-	5	-	ns	I _D =100mA, V _{DD} ≒ 25V
Rise time	t _r *	-	8	-	ns	V _{GS} =4.5V
Turn-off delay time	t _{d(off)} *	-	17	-	ns	$R_L=250\Omega$
Fall time	t _f *	-	43	-	ns	$R_G=10\Omega$

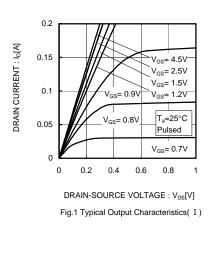
^{*}Pulsed

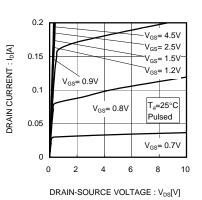
●Body diode characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V _{SD} *	-	-	1.2	V	I _s =200mA, V _{GS} =0V

^{*}Pulsed

Electrical characteristics curves





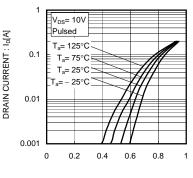


Fig.2 Typical Output Characteristics(II)

GATE-SOURCE VOLTAGE: V_{GS}[V] Fig.3 Typical Transfer Characteristics

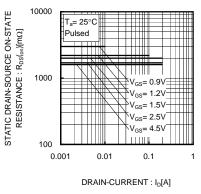


Fig.4 Static Drain-Source On-State

Resistance vs. Drain Current(I)

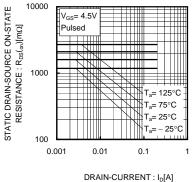


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

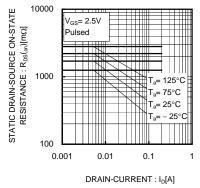


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)

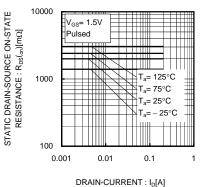


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

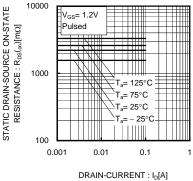


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current(V)

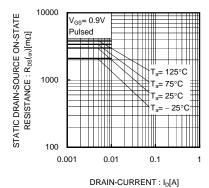


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current(VI)

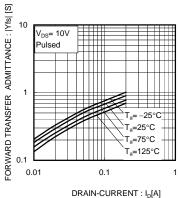


Fig.10 Forward Transfer Admittance
vs. Drain Current

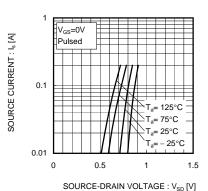


Fig.11 Reverse Drain Current vs. Sourse-Drain Voltage

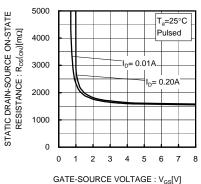


Fig.12 Static Drain-Source On-State
Resistance vs. Gate Source Voltage

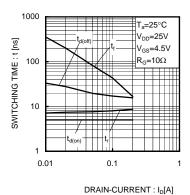
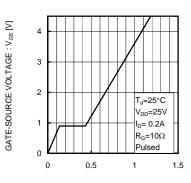
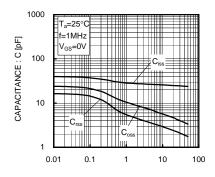


Fig.13 Switching Characteristics



TOTAL GATE CHARGE : Qg [nC]
Fig.14 Typical Capacitance

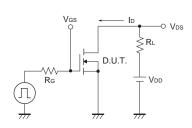
vs. Drain-Source Voltage



DRAIN-SOURCE VOLTAGE : V_{DS}[V]

Fig.15 Typical Capacitance
vs. Drain-Source Voltage

Measurement circuits





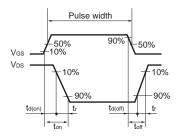


Fig.1-2 Switching Waveforms

Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

Notes

No copying or reproduction of this document, in part or in whole, is permitted without the consent of ROHM Co.,Ltd.

The content specified herein is subject to change for improvement without notice.

The content specified herein is for the purpose of introducing ROHM's products (hereinafter "Products"). If you wish to use any such Product, please be sure to refer to the specifications, which can be obtained from ROHM upon request.

Examples of application circuits, circuit constants and any other information contained herein illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.

Great care was taken in ensuring the accuracy of the information specified in this document. However, should you incur any damage arising from any inaccuracy or misprint of such information, ROHM shall bear no responsibility for such damage.

The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM and other parties. ROHM shall bear no responsibility whatsoever for any dispute arising from the use of such technical information.

The Products specified in this document are intended to be used with general-use electronic equipment or devices (such as audio visual equipment, office-automation equipment, communication devices, electronic appliances and amusement devices).

The Products specified in this document are not designed to be radiation tolerant.

While ROHM always makes efforts to enhance the quality and reliability of its Products, a Product may fail or malfunction for a variety of reasons.

Please be sure to implement in your equipment using the Products safety measures to guard against the possibility of physical injury, fire or any other damage caused in the event of the failure of any Product, such as derating, redundancy, fire control and fail-safe designs. ROHM shall bear no responsibility whatsoever for your use of any Product outside of the prescribed scope or not in accordance with the instruction manual.

The Products are not designed or manufactured to be used with any equipment, device or system which requires an extremely high level of reliability the failure or malfunction of which may result in a direct threat to human life or create a risk of human injury (such as a medical instrument, transportation equipment, aerospace machinery, nuclear-reactor controller, fuel-controller or other safety device). ROHM shall bear no responsibility in any way for use of any of the Products for the above special purposes. If a Product is intended to be used for any such special purpose, please contact a ROHM sales representative before purchasing.

If you intend to export or ship overseas any Product or technology specified herein that may be controlled under the Foreign Exchange and the Foreign Trade Law, you will be required to obtain a license or permit under the Law.



Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by ROHM manufacturer:

Other Similar products are found below:

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW216A-TL-2W FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3